

CONTENTS

An Analysis of Line-Width Control in Plasma Etched Polysilicon Using Response Surface Methodology	1
T. Abraham and T. Webster, Canada	
The Behavior of Matter in Strong Electric Fields— Field Chemistry and Related Problems	15
Karl P. Wissneroth, West Germany	
Synthesis of Ultrafine Silicon Nitride in an RF Plasma Reactor	71
T. Hussain and V. J. Ibbsen, England	
The Role of Glow Discharge in the Formation of a Boride Layer on Steel in the Plasma Boriding Process	79
T. Wierzchoń, Poland	
Reactor and Equipment Designs in Low-Temperature Plasma Technology	89
Herman V. Boenig, U.S.A.	
Synthesis of Zn-Sn Alloys in a Glow Discharge	205
T. J. Lin, T. J. O'Keefe and W. J. James, U.S.A.	
Low Temperature Plasma Modification of Polysiloxanes	229
M. de Mendez, J. C. Boeda, G. Legeay, J. C. Brosse, and P. Simon, France	
IR Spectra ($50\text{--}4000\text{ cm}^{-1}$) of Ultrathin Plasma SiO_2	243
L. I. Popova and E. D. Atanassova, Bulgaria	
Inversion Channel Transport Properties of Plasma Treated Si-SiO_2 Structures with Different Oxide Thicknesses	249
J. Kassabov, E. Atanassova, and E. Goranova, Bulgaria	

**Electric Activation of the Gaseous Medium in the Plasma
Titanizing Process.....**

.275

T. Wierzchoń and S. Pokrasen, Poland